

FGW30N120HD

Discrete IGBT

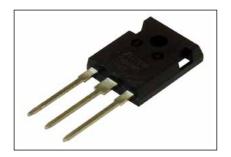
Discrete IGBT (High-Speed V series) 1200V / 30A

■ Features

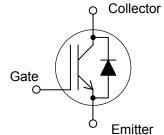
Low power loss Low switching surge and noise High reliability, high ruggedness (RBSOA, SCSOA etc.)

Applications

Uninterruptible power supply Power coditionner Power factor correction circuit



Equivalent circuit



■ Maximum Ratings and Characteristics

● Absolute Maximum Ratings (at T_c=25°C unless otherwise specified)

Items	Symbols	Characteristics	Units	Remarks
Collector-Emitter Voltage	Vces	1200	V	
Gate-Emitter Voltage	V _{GES}	±20	V	
DC Collector Current	I _{C@25}	53	Α	Tc=25°C,Tj=150°C
	Ic@100	30	Α	Tc=100°C,Tj=150°C
Pulsed Collector Current	I _{CP}	90	Α	Note *1
Turn-Off Safe Operating Area	-	90	Α	Vce≤1200V,Tj≤175°C
Diode Forward Current	I _{F@25}	36	Α	
	IF@100	20	Α	
Diode Pulsed Current	IFP	90	Α	Note *1
Short Circuit Withstand Time	tsc	5	ше	Vcc≤600V,VgE=12V
		3	μs	T _j ≤150°C
IGBT Max. Power Dissipation	P _{D_IGBT}	260	W	Tc=25°C
FWD Max. Power Dissipation	P _{D_FWD}	125	VV	Tc=25°C
Operating Junction Temperature	T _j	-40 ~ +175	ů	
Storage Temperature	T _{stg}	-55 ~ +175	°C	

Note *1 : Pulse width limited by Tjmax.

● Electrical characteristics (at T_i= 25°C unless otherwise specified)

Items	Cumbala	Symbols Conditions			Characteristics		
items	Symbols	Conditions		min.	typ.	max.	Units
Collector-Emitter Breakdown Voltage	V _{(BR)CES}	Ic = 50μA, V _{GE} = 0V		1200	-	-	V
Zero Gate Voltage Collector Current	Ices		T _i =25°C	-	-	250	μA
	TOES	<u> </u>	T _j =175°C	-	-	2	mA
Gate-Emitter Leakage Current	IGES	$V_{CE} = 0V, V_{GE} = \pm 20V$		-	-	200	nA
Gate-Emitter Threshold Voltage	V _{GE (th)}	$V_{CE} = +20V, I_{C} = 30mA$		4.0	5.0	6.0	V
Collector-Emitter Saturation Voltage	V _{CE} (sat)	V _{GE} = +15V, I _C = 30A	T _i =25°C	-	1.8	2.34	V
			T _i =175°C	-	2.3	-	v
Input Capacitance	Cies		V _{CE} =25V		2350	-]
Output Capacitance	Coes	V _{GE} =0V		-	105	-	pF
Reverse Transfer Capacitance	Cres	f=1MHz		-	80	-	
		Vcc = 600V					
Gate Charge	Q _G	Ic = 30A	-	230	-	nC	
		V _{GE} = 15V					
Turn-On Delay Time	t _{d(on)}	$T_i = 25^{\circ}C$	-	28	-	ns	
Rise Time	t	Vcc = 600V	-	28	-		
Turn-Off Delay Time	t _{d(off)}	Ic = 30A	-	260	-		
Fall Time	tr	V _{GE} = 15V	-	38	-		
Turn-On Energy	Eon	R _G = 10Ω	-	1.6	-		
•		L = 500µH	L = 500µH				mJ
Turn-Off Energy	Eoff	Energy loss include "tail" and	-	1.5	-	1110	
		recovery.					
Turn-On Delay Time	t _{d(on)}	T _j = 175°C		-	30	-	
Rise Time	t	Vcc = 600V	-	30	-	ns	
Turn-Off Delay Time	t _{d(off)}	Ic = 30A	-	300	-		
Fall Time	tr	V _{GE} = 15V	-	65	-		
Turn-On Energy	Eon	$R_G = 10\Omega$		-	2.8	-	
-		L = 500µH					mJ
Turn-Off Energy	Eoff	Energy loss include "tail" and	-	2.5 -	1113		
		recovery.					

http://www.fujielectric.com/products/semiconductor/

● FWD Characteristics

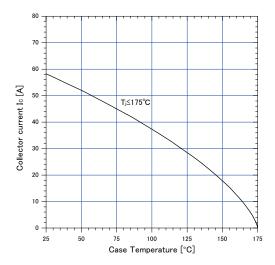
Description	Symbol	Conditions	Conditions		Characteristics		
Description Sym		Conditions			typ.	max.	Unit
Forward Voltage Drop	VF	I _F =20A	T _i =25°C	-	2.2	2.8	V
	VF	IF-2UA	T _i =175°C	-	1.8	-	V
Diode Reverse Recovery Time	4	Vcc=30V,I _F = 2.0A			42	55	ns
	t rr1	-di/dt=200A/µs					
Diode Reverse Recovery Time	t _{rr2}	Vcc=600V			0.38	_	μs
Diode Neverse Necovery Time	UTZ	I==20A			0.50		μο
Diode Reverse Recovery Charge	Qrr	-di₅/dt=200A/μs		_	0.95	-	μC
Blode Novelee Necestery Charge	Q.	T _j =25°C					
Diode Reverse Recovery Time	t _{rr2}	Vcc=600V		_	0.66	_	μs
	5.2	I _F =20A			0.00		F-0
Diode Reverse Recovery Charge	Qrr	-di⊧/dt=200A/μs		_	4.5	_	μC
	•	T _i =175°C			7.5	_	μΟ

● Thermal resistance characteristics

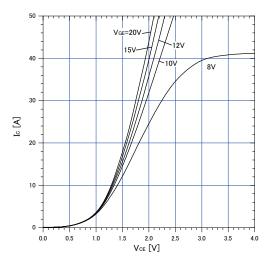
Items	Symbols	Conditions	Characteristics			Units
			min.	typ.	max.	Units
Thermal Resistance, Junction-Ambient	R _{th(j-a)}	-	-	-	50	
Thermal Resistance, IGBT Junction to Case	R _{th(j-c)_IGBT}	-	-	-	0.568	°C/W
Thermal Resistance, FWD Junction to Case	R _{th(j-c)_FWD}	-	-	-	1.191	

■ Characteristics (Representative)

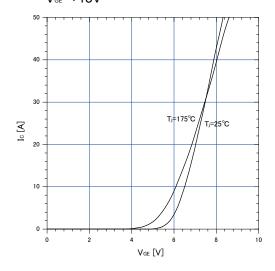
Graph.1 DC Collector Current vs T_c $V_{ce} \ge +15V$, $T_i \le 175$ °C



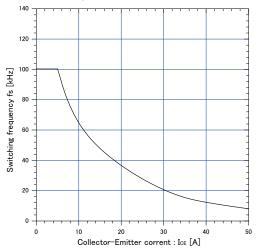
Graph.3
Typical Output Characteristics (VcE-lc)
T,=25°C



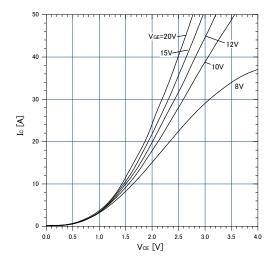
Graph.5 Typical Transfer Characteristics V_{GE} =+15V



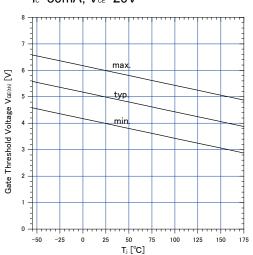
Graph.2 Collector Current vs. switching frequency V_{GE} =+15V, T_{C} ≤175°C, V_{CC} =600V, D=0.5, R_{G} =10 Ω , T_{C} =100°C



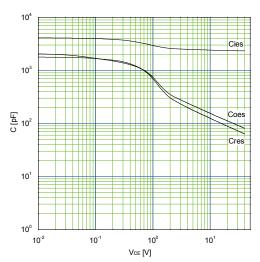
Graph.4
Typical Output Characteristics (VcE-Ic)
T_i=175°C



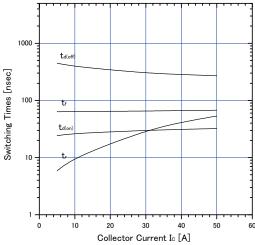
Graph.6
Gate Threshold Voltage vs. T₁
I₀=30mA, V₀∈=20V



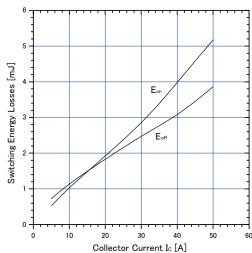
Graph.7 Typical Capacitance $V_{\text{GE}}=0V,f=1MHz,T,=25^{\circ}C$



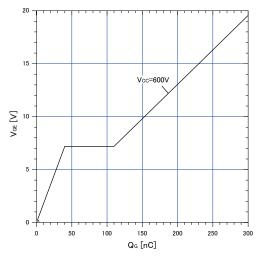
Graph.9 Typical switching time vs. I_c T_J=175°C,V_{cc}=600V,L=500 μ H V_{GE}=15V,R_G=10 Ω



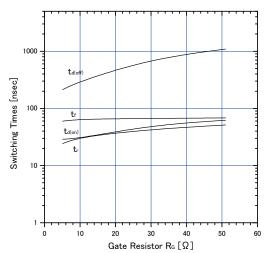
Graph.11 Typical switching losses vs. Io $T_{\rm J}$ =175°C, $V_{\rm CC}$ =600V,L=500 μ H $V_{\rm GE}$ =15V, $R_{\rm G}$ =10 Ω



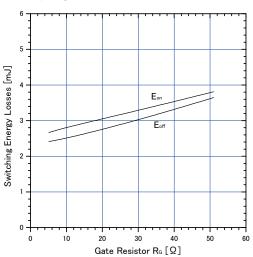
Graph.8 Typical Gate Charge Vcc=600V,Ic=30A,Tj=25°C



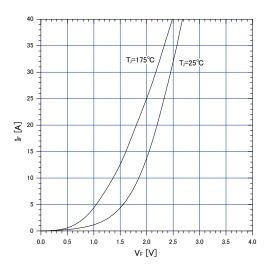
Graph.10
Typical switching time vs. R_s
T_i=175°C,V_{cc}=600V,I_c=30A,L=500μH
V_{se}=15V



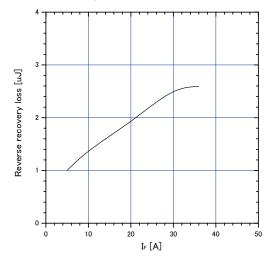
Graph.12 Typical switching losses vs. R_s T_j =175°C, V_{cc} =600V, I_c =30A,L=500 μ H V_{ce} =15V



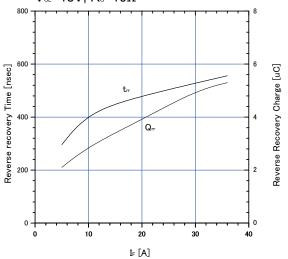
Graph.13 FWD Forward voltage drop $(V_F - I_F)$



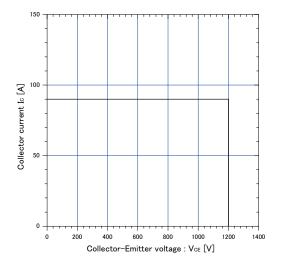
Graph.15 Typical reverse recovery loss vs. I_F T_J=175°C, V_{cc} =600V, L=500 μ H V_{ce} =15V, R_c =10 Ω



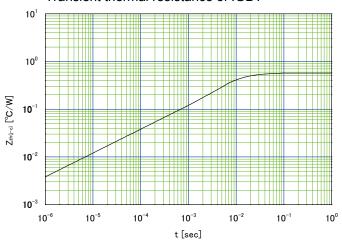
Graph.14 Typical reverse recovery characteristics vs. I_{F} T_{J} =175°C, V_{cc} =600V, L=500 μH V_{ce} =15V, R_{c} =10 Ω



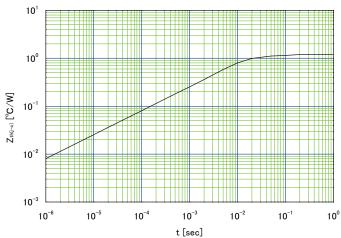
Graph.16
Reverse biased Safe Operating Area $T_1 \le 175^{\circ}C$, $V_{\odot} = +15V/0V$, $R_{\odot} = 10\Omega$



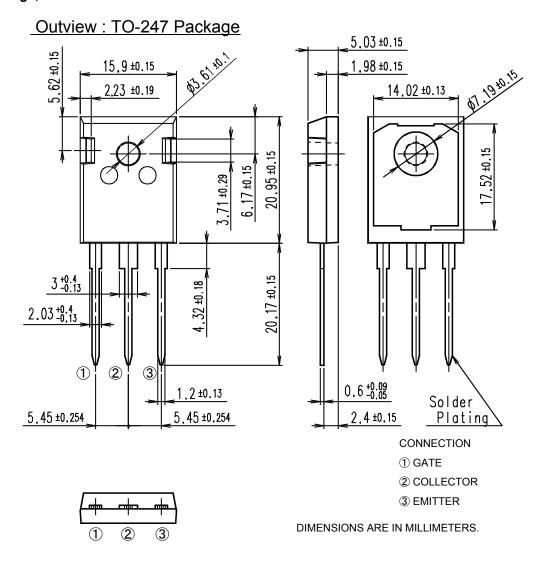
Graph.17 Transient thermal resistance of IGBT



Graph.18
Transient thermal resistance of FWD



■ Outline Drawings, mm



WARNING

- 1. This Catalog contains the product specifications, characteristics, data, materials, and structures as of May 2011. The contents are subject to change without notice for specification changes or other reasons. When using a product listed in this Catalog, be sur to obtain the latest specifications.
- 2. All applications described in this Catalog exemplify the use of Fuji's products for your reference only. No right or license, either express or implied, under any patent, copyright, trade secret or other intellectual property right owned by Fuji Electric Co., Ltd. is (or shall be deemed) granted. Fuji Electric Co., Ltd. makes no representation or warranty, whether express or implied, relating to the infringement or alleged infringement of other's intellectual property rights which may arise from the use of the applications described herein.
- 3. Although Fuji Electric Co., Ltd. is enhancing product quality and reliability, a small percentage of semiconductor products may become faulty. When using Fuji Electric semiconductor products in your equipment, you are requested to take adequate safety measures to prevent the equipment from causing a physical injury, fire, or other problem if any of the products become faulty. It is recommended to make your design failsafe, flame retardant, and free of malfunction.
- 4. The products introduced in this Catalog are intended for use in the following electronic and electrical equipment which has normal reliability requirements.
 - Computers
- OA equipment
- Communications equipment (terminal devices)
- Measurement equipment

- · Machine tools
- Audiovisual equipment
- Electrical home appliances • Personal equipment • Industrial robots etc.
- 5. If you need to use a product in this Catalog for equipment requiring higher reliability than normal, such as for the equipment listed below, it is imperative to contact Fuji Electric Co., Ltd. to obtain prior approval. When using these products for such equipment, take adequate measures such as a backup system to prevent the equipment from malfunctioning even if a Fuji's product incorporated in the equipment becomes faulty.
- Transportation equipment (mounted on cars and ships)
- Trunk communications equipment

• Traffic-signal control equipment

- · Gas leakage detectors with an auto-shut-off feature
- Emergency equipment for responding to disasters and anti-burglary devices
- · Safety devices
- · Medical equipment
- (without limitation). Aeronautic equipment · Nuclear control equipment
- Space equipment • Submarine repeater equipment
- 7. Copyright ©1996-2011 by Fuji Electric Co., Ltd. All rights reserved.

No part of this Catalog may be reproduced in any form or by any means without the express permission of Fuji Electric Co., Ltd.

8. If you have any question about any portion in this Catalog, ask Fuji Electric Co., Ltd. or its sales agents before using the product. Neither Fuji Electric Co., Ltd. nor its agents shall be liable for any injury caused by any use of the products not in accordance with instructions set forth herein.

6. Do not use products in this Catalog for the equipment requiring strict reliability such as the following and equivalents to strategic equipment

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for fuji manufacturer:

Other Similar products are found below:

BZ6WL30CU BZ6WR30CAU BZ6WL30CAU EW100AAG-3P100B EW50AAG-2P015B FMN-60 5V AH165-EG33 AH165-J3C33A

AH165-SGLW11E3 AH165-TGL5W11E3 AHX511-L AHX662-A DR30D0L-E3A AR22E0L-10E4G AR22F0L-02H4R AR22G3R-01B

AR22G4L-10E3W AR22G4L-11E3A AR22JCR-3A14DC AR22M0R-01B AR22PR-711B AR22S2R-22W AR22VGE-11R AR30E0L
10E3W AR30E0R-11G AR9T511-H EG52F/40-30MA BU-ECA2005L BW9BTAA-L3 BW9BTAA-S2 BW9FWCA-15A BZ6KL10CU

1TR0AK RT11-DC24V SA103RCUL/60 SA103RCUL/75 SA203CUL/125 SA203CUL/200 SA203RCUL/125 SA53RCUL/3 SC-E1
220VAC SC-E5-200V 2NC2F-CK SG103CUL/40-CO SK12LR-E01W AC09-CX0/11L1 EW125JAG-4P030K EW250JAGU-3P200K

EW250JAGU-3P225K EW50RAGU-3P003K